



**CMSSH-3**  
**CMSSH-3A**  
**CMSSH-3C**  
**CMSSH-3S**

**SUPER-MINI**  
**SCHOTTKY DIODES**

**SUPER**<sup>TM</sup>  
**mini**



**SOT-323 CASE**

## DESCRIPTION

The CENTRAL SEMICONDUCTOR CMSSH-3 Series types are Silicon Schottky diodes, epoxy molded in a super-mini surface mount package, designed for fast switching applications requiring a low forward voltage drop.

The following configurations are available:

CMSSH-3	SINGLE
CMSSH-3A	DUAL, COMMON ANODE
CMSSH-3C	DUAL, COMMON CATHODE
CMSSH-3S	DUAL, IN SERIES

**MARKING CODE: 95D**  
**MARKING CODE: B1D**  
**MARKING CODE: B2D**  
**MARKING CODE: A5D**

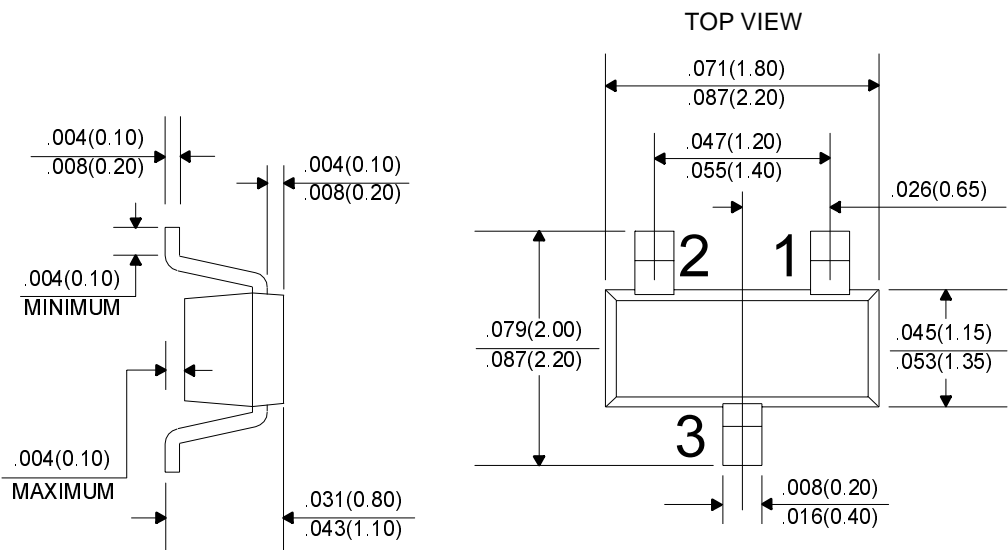
## MAXIMUM RATINGS (T<sub>A</sub>=25°C)

	SYMBOL		UNITS
Peak Repetitive Reverse Voltage	V <sub>RRM</sub>	30	V
Continuous Forward Current	I <sub>F</sub>	100	mA
Peak Repetitive Forward Current	I <sub>FRM</sub>	350	mA
Forward Surge Current, tp=10ms	I <sub>FSM</sub>	750	mA
Power Dissipation	P <sub>D</sub>	250	mW
Operating and Storage			
Junction Temperature	T <sub>J</sub> , T <sub>stg</sub>	-65 to +150	°C
Thermal Resistance	θ <sub>JA</sub>	500	°C/W

## ELECTRICAL CHARACTERISTICS (T<sub>A</sub>=25°C unless otherwise noted)

SYMBOL	TEST CONDITIONS	MIN	TYP	MAX	UNIT
B <sub>V</sub> R	I <sub>R</sub> =100μA	30			V
V <sub>F</sub>	I <sub>F</sub> =2.0mA		0.29	0.33	V
V <sub>F</sub>	I <sub>F</sub> =15mA		0.40	0.45	V
V <sub>F</sub>	I <sub>F</sub> =100mA		0.74	1.00	V
I <sub>R</sub>	V <sub>R</sub> =25V		90	500	nA
I <sub>R</sub>	V <sub>R</sub> =25V, T <sub>A</sub> =100°C		25	100	μA
C <sub>T</sub>	V <sub>R</sub> =1.0V, f=1 MHz		7.0		pF
t <sub>rr</sub>	I <sub>F</sub> =I <sub>R</sub> =10mA, I <sub>rr</sub> =1.0mA, R <sub>L</sub> =100Ω			5.0	ns

All Dimensions in Inches (mm).



Lead Code

